

IN THE CLAIMS

1-5. (Withdrawn).

6. (Original) A method of manufacturing a semiconductor device comprising the steps of:

(a) providing a first mold having a main surface, and a second mold having a main surface and having a first concaved portion on the main surface;

(b) providing a resin containing plural particles;

(c) providing a sheet having plural openings each having a diameter larger than that of the particle and through holes each having a diameter larger than that of the plural openings;

(d) opposing and contacting the main surface of the first mold and the main surface of the second mold to each other, and disposing the sheet between the main surface of the first mold and the main surface of the second mold to position the through holes at the openings surrounded with the main surface of the first mold and the first concaved portion;

(e) after the step (d), injecting a resin to an inside of the openings surrounded with the main surface of the first mold and the first concaved portion;

(f) after the step (e), removing the sheet on the main surface of the first mold and the second mold and the resin;

(g) after the step (f), opposing and contacting the main surface of the first mold and the main surface of the second mold to each other and disposing a semiconductor chip to the inside of the opening surrounded with the main surface of the first mold and the first concaved portion; and

(h) after the step (g), filling an encapsulating resin to the inside of the opening surrounded with the main surface of the first mold and first concaved portion thereby encapsulating the semiconductor chip.

7. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the sheet is a non-woven fabric, paper or net-like material.

8. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the sheet is formed with plural openings each having a diameter larger than that of the particle over an entire surface of the sheet.

9. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the second die has a second concaved portion on the main surface and the step (e) comprises a step of disposing a resin containing the plural particles to the inside of the second concaved portion and a step of applying heat and pressure to the resin and charging the same to the inside of the openings.

10. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the particles are formed of silica.

11. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the resin portion of the resin containing the particles is formed of a melamine resin.

12. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the method further comprises, before the step (d), the steps of:

(i) opposing and contacting the main surface of the first mold and the main surface of the second mold and disposing a semiconductor chip to an inside of the opening

surrounded with the main surface of the first mold and the first concaved portion; and

(j) after the step (i), filling an encapsulating resin to the inside of the opening surrounded with the main surface of the first mold and the first concaved portion and encapsulating the semiconductor chip.

13. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

(a) providing a first mold having a main surface, and a second mold having a main surface and provided with first and second concaved portions on the main surface;

(b) providing a resin containing plural particles;

(c) providing a sheet having plural openings each having a diameter larger than that of the particle and through holes each having a diameter larger than that of the plural openings;

(d) opposing and contacting the main surface of the first mold and the main surface of the second mold and disposing the sheet between the main surface of the first mold and the main surface of the second mold to situate the first and the second concaved portions in the region where the through holes are disposed;

(e) after the step (d), injecting a resin to the inside of the openings surrounded with the main surface of the first mold and the first and second concaved portions;

(f) after the step (e), removing the sheet and the resin on the main surfaces of the first mold and the second mold;

(g) after the step (f), opposing and contacting the main surface of the first mold and the main surface of the second mold, disposing a first semiconductor chip at the inside of ~~the~~ a first opening surrounded with the main surface of the first mold and the first concaved portion, and disposing a second semiconductor chip to the inside of ~~the~~ a second opening surrounded with the main surface of the first mold and the second concaved portion; and

(h) after the step (g), filling an encapsulating resin to the inside of the first opening and the second opening, ~~surrounded with the main surface of the first mold and the first concaved portion~~ and encapsulating the first semiconductor chip and the second semiconductor chip with the encapsulating resin.